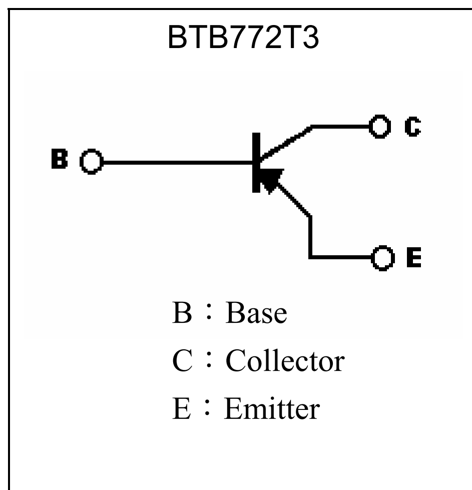
Low Vcesat PNP Epitaxial Planar Transistor

BTB772T3

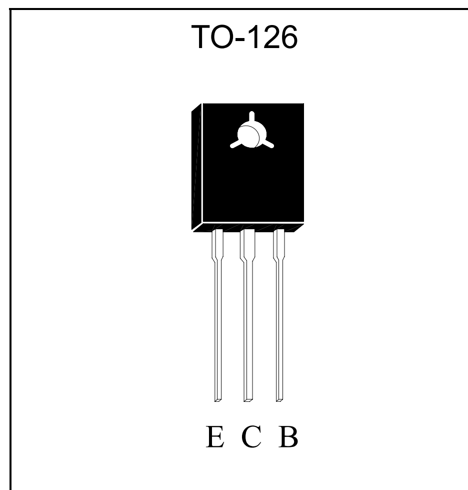
Features

- Low $V_{CE(sat)}$, typically -0.3V at I_C / I_B = -2A / -0.2A
- Excellent current gain characteristics
- Complementary to BTD882T3
- Pb-free lead plating and halogen-free package

Symbol

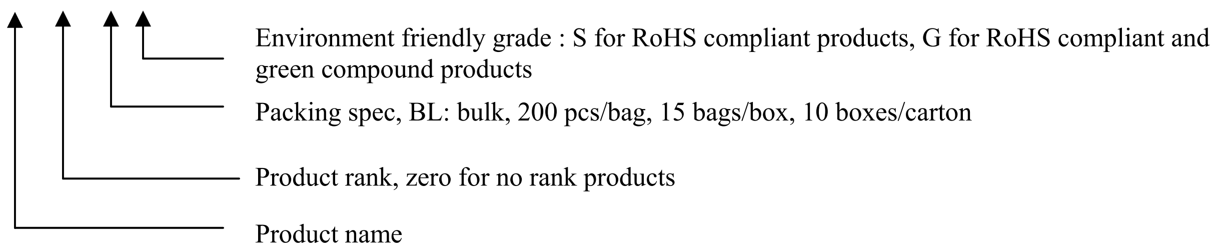


Outline



Ordering Information

Device	Package	Shipping
BTB772T3-P-BL-G	TO-126 (Pb-free lead plating and halogen-free package)	200 pcs / bag, 3,000 pcs/box 30,000 pcs/carton



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C(DC)	-3	A
	I_C(pulse)	-7 *1	A
Power Dissipation	Pd(Ta=25℃)	1	W
	Pd(Tc=25℃)	10	
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

Note : *1. Single Pulse Pw≦350μs, Duty≦2%.

Characteristics (Ta=25°C)

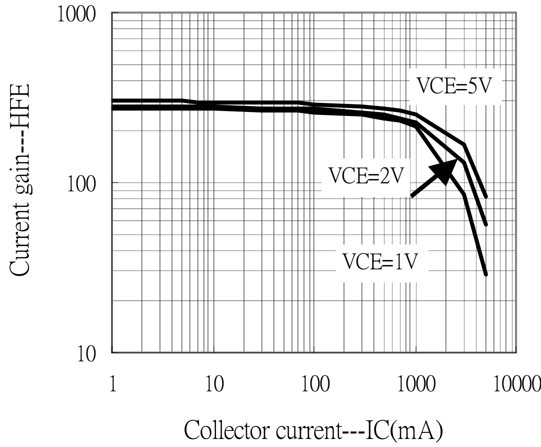
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-40	-	-	V	I_C=-50μA, I_E=0
BV_{CEO}	-30	-	-	V	I_C=-1mA, I_B=0
BV_{EBO}	-5	-	-	V	I_E=-50μA, I_C=0
I_{CBO}	-	-	-1	μA	V_{CB}=-30V, I_E=0
I_{EBO}	-	-	-1	μA	V_{EB}=-3V, I_C=0
*$V_{CE(sat)}$	-	-0.3	-0.5	V	I_C=-2A, I_B=-0.2A
*$V_{BE(sat)}$	-	-1	-2	V	I_C=-2A, I_B=-0.2A
*$h_{FE}1$	120	-	-	-	V_{CE}=-2V, I_C=-20mA
*$h_{FE}2$	180	-	390	-	V_{CE}=-2V, I_C=-1A
f_T	-	80	-	MHz	V_{CE}=-5V, I_C=-0.1A, f=100MHz
Cob	-	55	-	pF	V_{CB}=-10V, f=1MHz

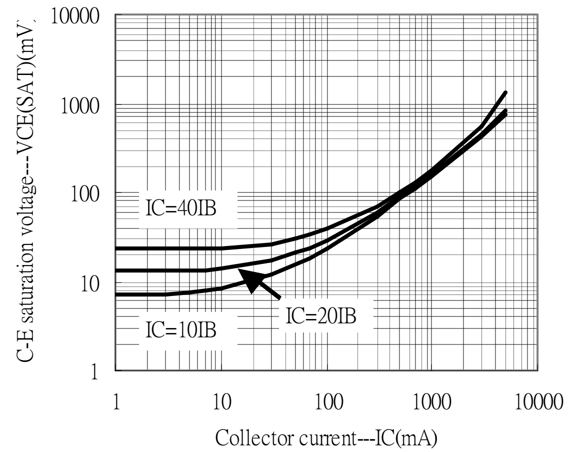
*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

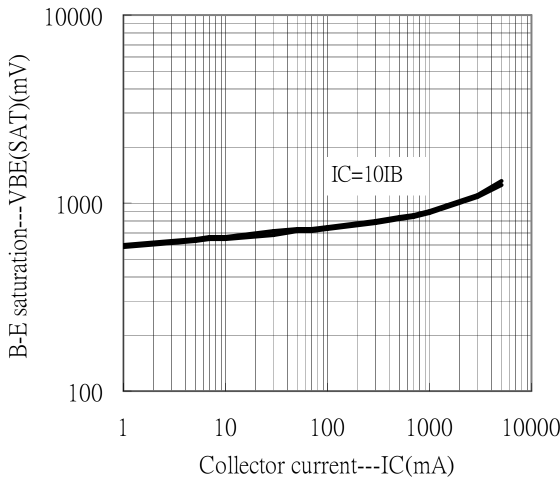
Classification Of hFE 2

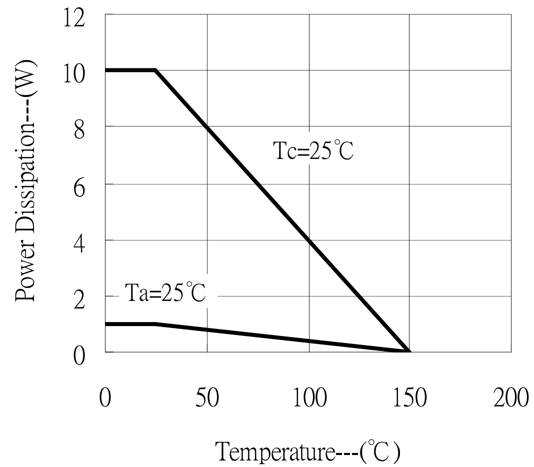
Rank	P
Range	180~390

Typical Characteristics





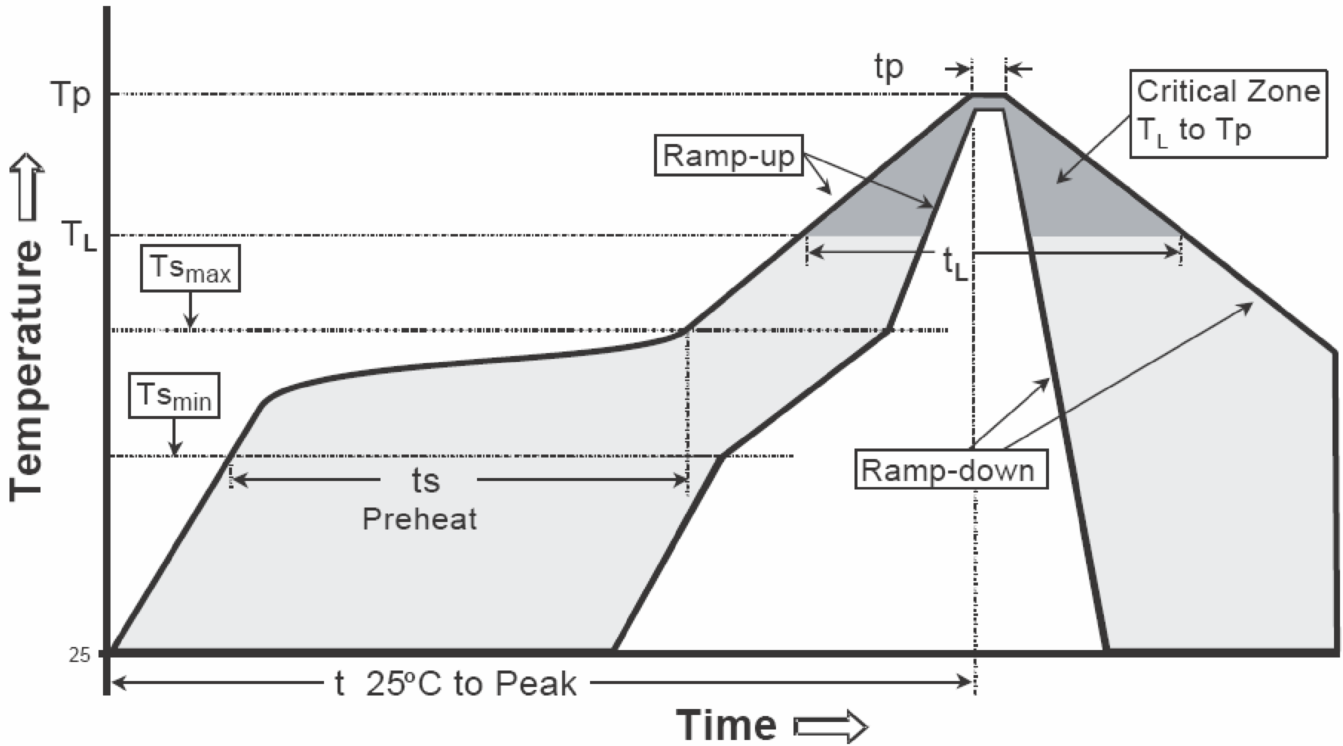




Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

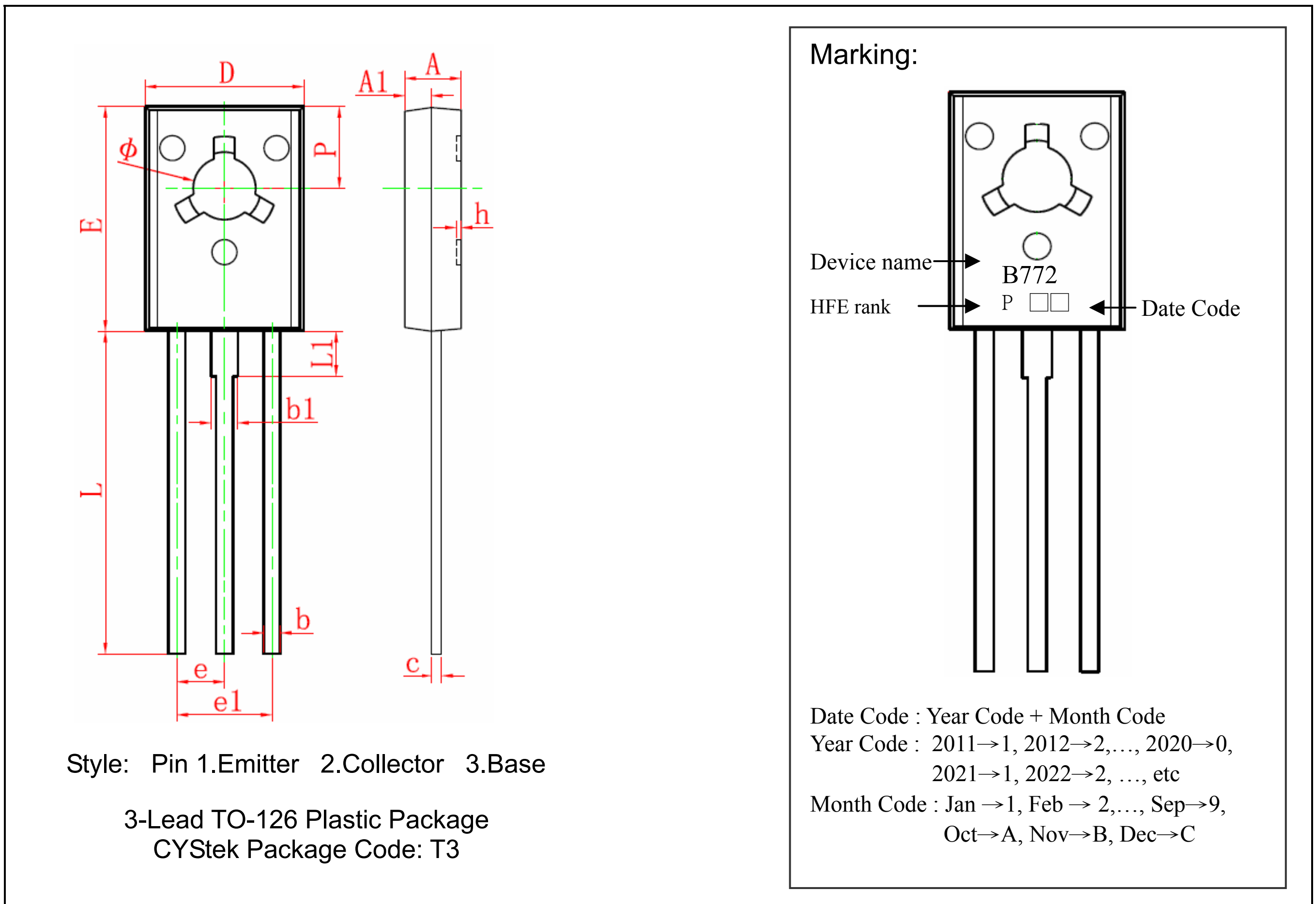
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(Ts min) −Temperature Max(Ts max) −Time(ts min to ts max)	 100°C 150°C 60-120 seconds	 150°C 200°C 60-180 seconds
Time maintained above: −Temperature (TL) − Time (tL)	 183°C 60-150 seconds	 217°C 60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-126 Dimension



Style: Pin 1.Emitter 2.Collector 3.Base

3-Lead TO-126 Plastic Package
CYStek Package Code: T3

*: Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	2.500	2.900	0.098	0.114	e	*2.290		*0.090	
A1	1.100	1.500	0.043	0.059	e1	4.480	4.680	0.176	0.184
b	0.660	0.860	0.026	0.034	h	0.000	0.300	0.000	0.012
b1	1.170	1.370	0.046	0.054	L	15.300	15.700	0.602	0.618
c	0.450	0.600	0.018	0.024	L1	2.100	2.300	0.083	0.091
D	7.400	7.800	0.291	0.307	P	3.900	4.100	0.154	0.161
E	10.600	11.000	0.417	0.433	Φ	3.000	3.200	0.118	0.126

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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